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PATENT APPLICATION

2-8-00
M. H. H. H.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Hiroyuki ABE and Mitsutoshi MIYASAKA

Application No.: PCT-US National Stage of PCT/JP97/00213

Filed: September 30, 1997

Docket No.: JAO 39514

For: HIGH ENERGY SUPPLY APPARATUS, METHOD OF FORMING
CRYSTALLINE FILM AND METHOD OF MANUFACTURING THIN FILM
ELECTRONIC DEVICE

PRELIMINARY AMENDMENT

Assistant Commissioner of Patents
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE ABSTRACT:

Please replace the Abstract with the substitute Abstract appended hereto.

IN THE SPECIFICATION:

Please replace the Specification with the substitute Specification appended hereto.

IN THE CLAIMS:

Please amend claims 1-62 as follows:

1. (Amended) A method of forming a crystalline film, comprising the steps of:

[a first step of] forming a thin film on a substrate[,]; and

[a second step of] crystallizing at least [the] a surface layer of the thin film, [wherein;] such that [in the second steps,] at least the surface layer of the thin film is melted and crystallized under a hydrogen-containing atmosphere.

2. (Amended) [A] The method of forming a crystalline film according to Claim 1, wherein the thin film is a semiconductor thin film.

[3. (Amended) [A] The method of forming a

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